

TSH321

WIDE BANDWIDTH AND MOS INPUT SINGLE OPERATIONAL AMPLIFIER

LOW DISTORTION

- GAIN BANDWIDTH PRODUCT : 300MHz
- GAIN OF 2 STABILITY
- SLEW RATE : 400V/µs
- VERY FAST SETTLING TIME : 60ns (0.1%)
- VERY HIGH INPUT IMPEDANCE

DESCRIPTION

The TSH321 is a wideband monolithic operational amplifier, requiring a minimum close loop gain of 2 for stability.

The TSH321 features extremely high input impedance (typically greater than $10^{12}\Omega$) allowing direct interfacing with high impedance sources.

Low distortion, wide bandwidth and high linearity make this amplifier suitable for RF and video applications. Short circuit protection is provided by an internal current-limiting circuit.

The TSH321 has internal electrostatic discharge (ESD) protection circuits and fulfills MILSTD883C-Class2.

ORDER CODE

Part Number	Ton pora ure Range	Packane
TSH321I	-40°C, +125°C	•

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SCHEMATIC DIAGRAM



MAXIMUM PATINGS

Symbo'	Parameter	Value	Unit
.'/ _{CC}	Supply Voltage	±7	V
V _{id}	Differential Input Voltage	±5	V
Vi	Input Voltage	±5	V
l _{in}	Current On Offset Null Pins	±20	V
T _{oper}	Operating Free-Air Temperature range	-40 to +125	°C

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	±3 to ±6	V
V _{ic}	Common Mode Input Voltage Range	V_{CC}^{-} to V_{CC}^{+} -3	V

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Min.	Тур.	Max.	Unit
V _{io}	Input Offset Voltage T _{min} . ≤ T _{amb} ≤ T _{max}		0.5	10 12	mV
DV _{io}	Input Offset Voltage Drift T _{min} . ≤ T _{amb} ≤ T _{max.}		10		μV/°C
l _{ib}	Input Bias Current		2	300	pА
l _{io}	Input Offset Current		2	200	pA
I _{cc}	Supply Current, no load $\begin{array}{l} V_{CC}=\pm 5V\\ V_{CC}=\pm 3V\\ V_{CC}=\pm 6V\\ T_{min}.\leq T_{amb}\leq T_{max} \end{array}$		23 21 25	30 28 40 3. ⁻	mA
Avd	Large Signal Voltage Gain Vo = ± 2.5 V R _L = ∞ R _L = 100 Ω R _L = 50 Ω	800 300 200	1300 850 350	<u> </u>	V/V
V _{icm}	Input Common Mode Voltage Range	-5 to +2	5.5 to +2.5		V
CMR	Common-mode Rejection Ratio $V_{ic} = V_{icm min.}$	60	100		dB
SVR	Supply Voltage Rejection Ratio $V_{CC} = \pm 5V$ to $\pm 3V$	50	70	30	dB
V _o	$R_{L} = 100\Omega$ $R_{L} = 50\Omega$ $T_{min} \le T_{amb} \le T_{max}$ $R_{L} = 100\Omega$ $R_{L} = 50\Omega$	±3 ±2.8 ±2.9 ±2.7	+3.5 -3.7 +3.3 -3.5		V
Ι _ο	Output Short Circuit Current $\forall ia = \pm 1V$, $Vo = 0V$	±50	±100		mA
GBP	Gain Bandwidth Pr. Q.ict $A_{VCL} = 100$ R _L = 100 Ω , C _L = 15pF, f = 7.5MHz		300		MHz
SR	Slew Rate $V_{in} = \pm 1V$, $A_{VCL} = 2$, $R_L = 100\Omega$, $C_L = 15pF$	200	400		V/µs
en	Equivalent Input Voltage Noise $R_s = 50\Omega$ $f_o = 1kHz$ $f_o = 1kHz$ $f_o = 1kHz$ $f_o = 100kHz$ $f_o = 1MHz$		20 18.2 18.1 18.2		nV/√H:
K _{ov}	Overshoot $V_{in} = \pm 1V$, $A_{VCL} = 2$, $R_L = 100\Omega$, $C_L = 15pF$		15		%
ts	Settling Time 0.1% ¹⁾ $V_{in} = \pm 1V$, A _{VCL} = -1		60		ns
t _r , t _f	Rise and Fall Time (see note 1) $V_{in} = \pm 100 \text{mV}, A_{VCL} = 2$		2		ns
t _d	Delay Time (see note 1) V _{in} = ±100mV, A _{VCL} = 2		2		ns
φm	Phase Margin $A_{VM} = 2$, $R_L = 100\Omega$, $C_L = 15pF$		45		Degree
THD	Total Harmonic Distortion $A_{VCL} = 10$, f = 1kHz, $V_o = \pm 2.5V$, no load		0.02		%
FPB	Full Power Bandwidth ²⁾ Vo = 5Vpp, $R_L = 100\Omega$ Vo = 2Vpp, $R_L = 100\Omega$		26 64		MHz

 $V_{CC} = \pm 5V$, $T_{amb} = 25^{\circ}C$ (unless otherwise specified)

2. Full power bandwidth = <u>SR</u> П*V*орр

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TEST WAVEFORM



PRINTED CIRCUIT LAYOUT

As for any high frequency device, a few rules must be observed when designing the PCB to get the best performances from this high speed op amp.

From the most to the least important points :

- Each power supply lead has to be bypassed to ground with a 10μF cerainic capacitor very close to the device and a 10μF tantalum capacitor.
- To provide low incuc ance and low resistance common return, use a ground plane or common point return for power and signal.
- All reads must be wide and as short as possible especially for op amp inputs. This is in

EVALUATION CIRCUIT



- order to decrease parasitic capacitance and inductance.
- Use small resistor values to decrease time constant with parasitic capacitance.
- Choose component sizes as small as possible (SMD).
- On output, decrease capacitor load so as to avoid circuit stability being degraded which may cause oscillation. You can also add a serial resistor in order to minimise its influence.
- □ One can add in parallel with feedback resistor a few pF ceramic capacitor C_F adjusted to optimize the settling time.

PACKAGE MECHANICAL DATA

8 PINS - PLASTIC MICROPACKAGE (SO)



Dim.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α		101	1.75	S.		0.069
a1	0.1		0.25	0.004		0.010
a2	21		1.65			0.065
a3	0.65		0.85	0.026		0.033
b	0.35	S	0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
С	0.25		0.5	0.010		0.020
C			45° (typ.)		
5	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
е	2	1.27			0.050	
e3 🔷	(3.81			0.150	
F	3.8		4.0	0.150		0.157
L L	0.4		1.27	0.016		0.050
М			0.6			0.024
S	8° (max.)					

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